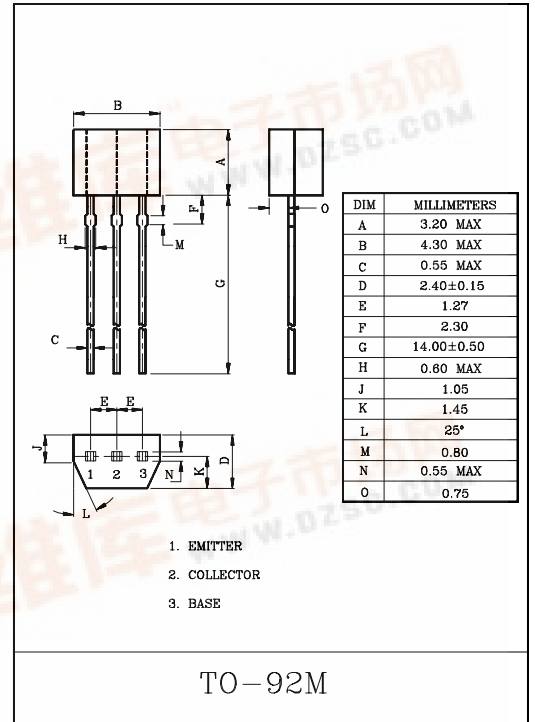
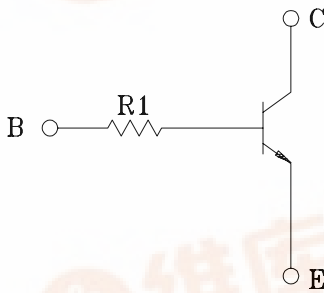


SWITCHING APPLICATION,  
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

**FEATURES**

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

**EQUIVALENT CIRCUIT**



**MAXIMUM RATINGS (Ta=25°C)**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Collector Current	$I_C$	100	mA
Collector Power Dissipation	$P_C$	400	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C

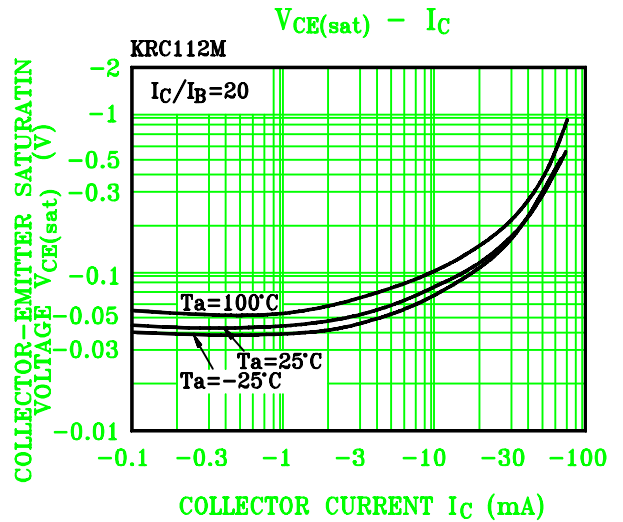
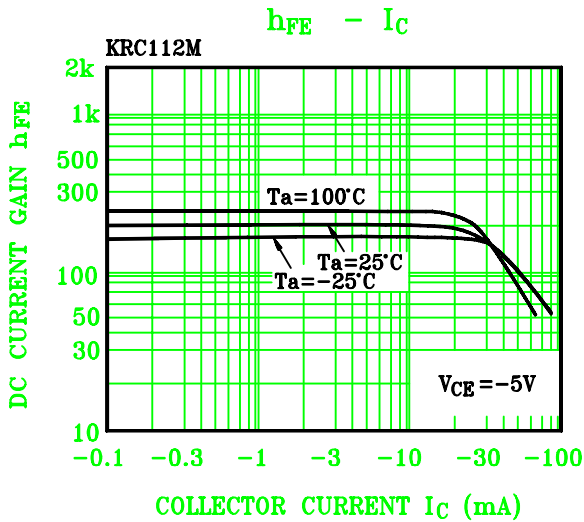
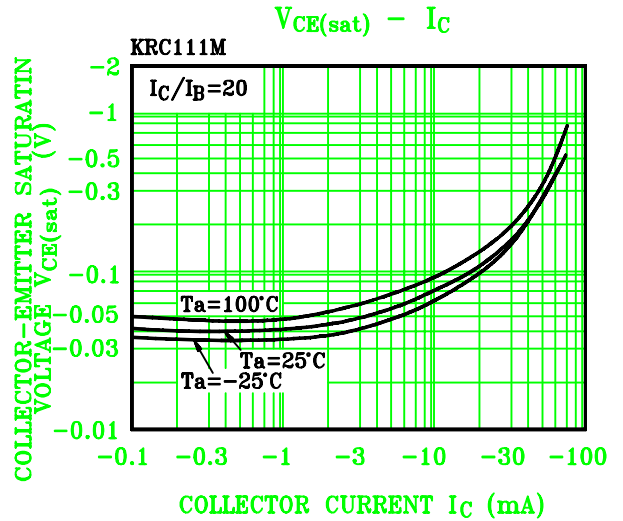
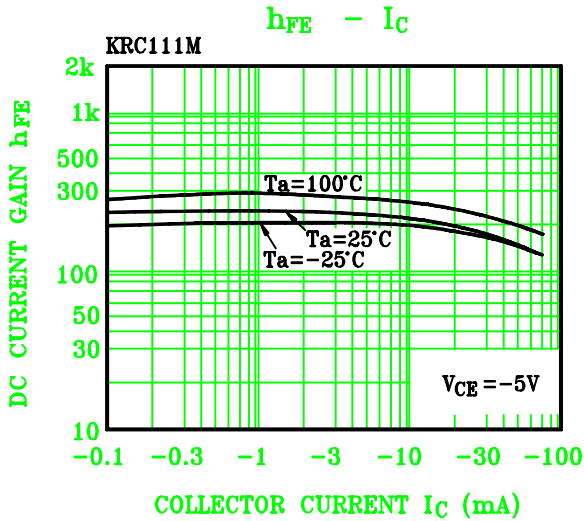
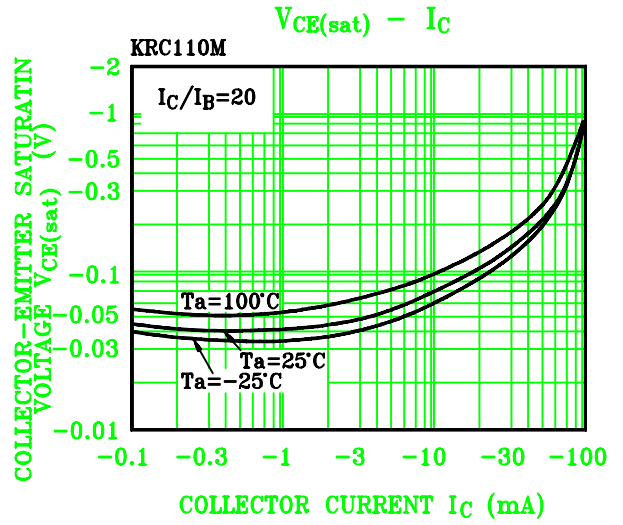
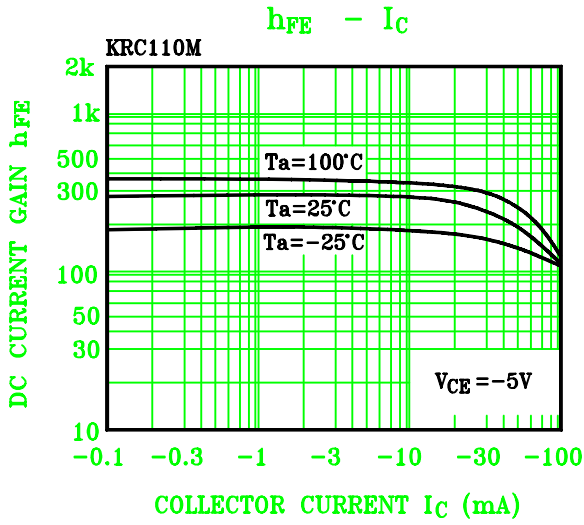
# KRC110M ~ KRC114M

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current		$I_{CBO}$	$V_{CB}=5V, I_E=0$	-	-	100	nA	
Emitter Cut-off Current		$I_{EBO}$	$V_{EB}=5V, I_C=0$	-	-	100	nA	
DC Current Gain		$h_{FE}$	$V_{CE}=5V, I_C=1mA$	120	-	-		
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=10mA, I_B=0.5mA$	-	0.1	0.3	V	
Transition Frequency		$f_T$ *	$V_{CE}=10V, I_C=5mA$	-	250	-	MHz	
Input Resistor	KRC110M	$R_i$		-	4.7	-	k $\Omega$	
	KRC111M			-	10	-		
	KRC112M			-	100	-		
	KRC113M			-	22	-		
	KRC114M			-	47	-		
Switching Time	Rise Time	$t_r$	$V_O=5V$ $V_{IN}=5V$ $R_L=1k\Omega$	-	0.025	-	$\mu S$	
				KRC111M	-	0.03		-
				KRC112M	-	0.3		-
				KRC113M	-	0.06		-
				KRC114M	-	0.11		-
	Storage Time	$t_{stg}$		KRC110M	-	3.0		-
				KRC111M	-	2.0		-
				KRC112M	-	6.0		-
				KRC113M	-	4.0		-
				KRC114M	-	5.0		-
	Fall Time	$t_f$		KRC110M	-	0.2		-
				KRC111M	-	0.12		-
				KRC112M	-	2.0		-
				KRC113M	-	0.9		-
				KRC114M	-	1.4		-

Note : \*Characteristic of Trnsistor Only

# KRC110M ~ KRC114M



# KRC110M~KRC114M

